TOSHIBA
Leading Innovation

TC35679FSG-002 New Product

Bluetooth® IC

Toshiba LE Gen-II ultra-low-power complete model
Suitable for coin-cell-operated data communication applications

Description

Feature	Ultra-low power / LE single / Scatternet support / Standalone mode support / Small QFN package / LE Data Length Extension support / LE Secure Connection supoort
Automotive Support	N/A
Bluetooth Category	Bluetooth® low energy
Bluetooth Core spec.	4.2
Embedded Profiles	GATT / SMP
Interfacing	I2C / SPI / UART / PWM / ADC / SWD
User RAM Size (KB)	83
Function	ARM® Cortex®-M0 / 50ohm impedance for RF IO / DC-DC converter / low power mode(4 level)
RoHS Compatible Product(s) (#)	Please contact us.
Status	New product

Properties

Package Information

Toshiba Package Name	P-VQFN40-0505-0.40-002
Package name	QFN
Pins	40
Package size	5.0 mm x 5.0 mm
Pin pitch	0.4 mm

Please refer to the link destination to check the detailed size.

Electrical Characteristics

Characteristics	Symbol	Condition	Value	Unit
Operating Temperature (Max)	T_{opr}	-	85	°C
Operating Temperature (Min)	T_{opr}	-	-40	°C
Power supply voltage (Max)	-	-	3.6	V
Power supply voltage (Min)	-	-	1.8	V
Current Consumption in RX Active mode (peak)	I_{RX}	(3.0V)	3.3	mA
Current Consumption in TX Active mode (peak)	I_{TX}	(3.0V, TX -0dBm)	3.3	mA
Current Consumption in Sleep mode	I_{Sleep}	-	1.7	µA
Current Consumption in Deep Sleep mode	I_{DSleep}	-	0.05	µA
Transmit Power(Max)	P_{Trans}	-	0	dBm
Receiver Sensitivity	-	-	-93	dBm